

FIG.1

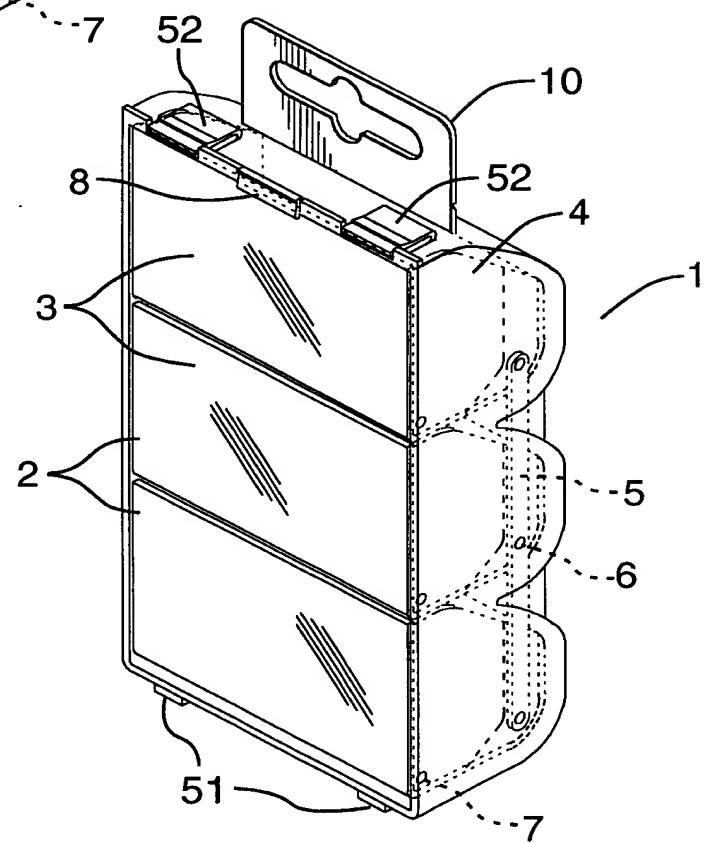


FIG.2

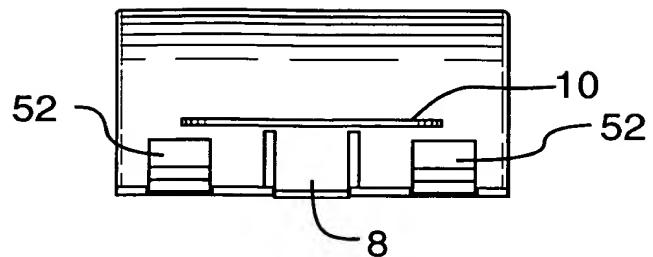


FIG.3

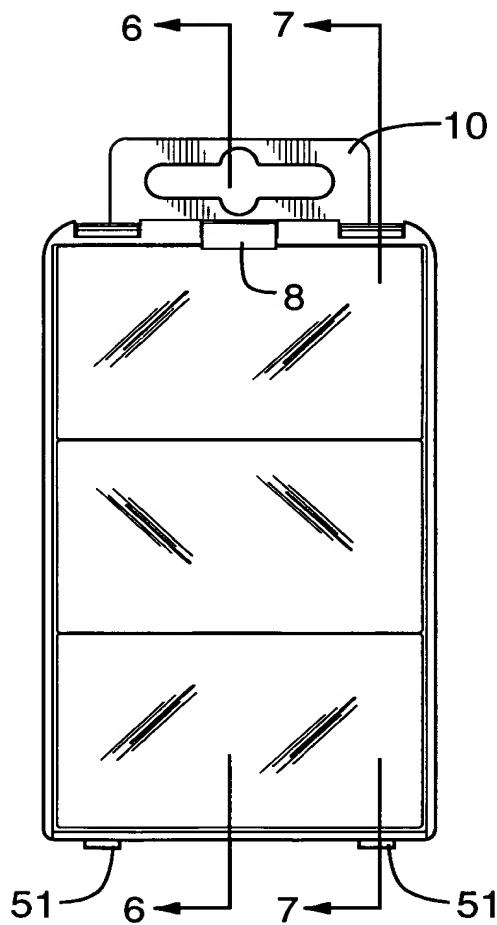


FIG.4

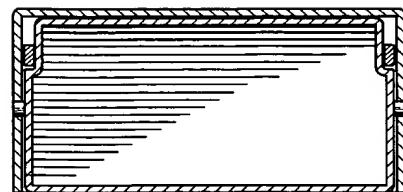


FIG.5

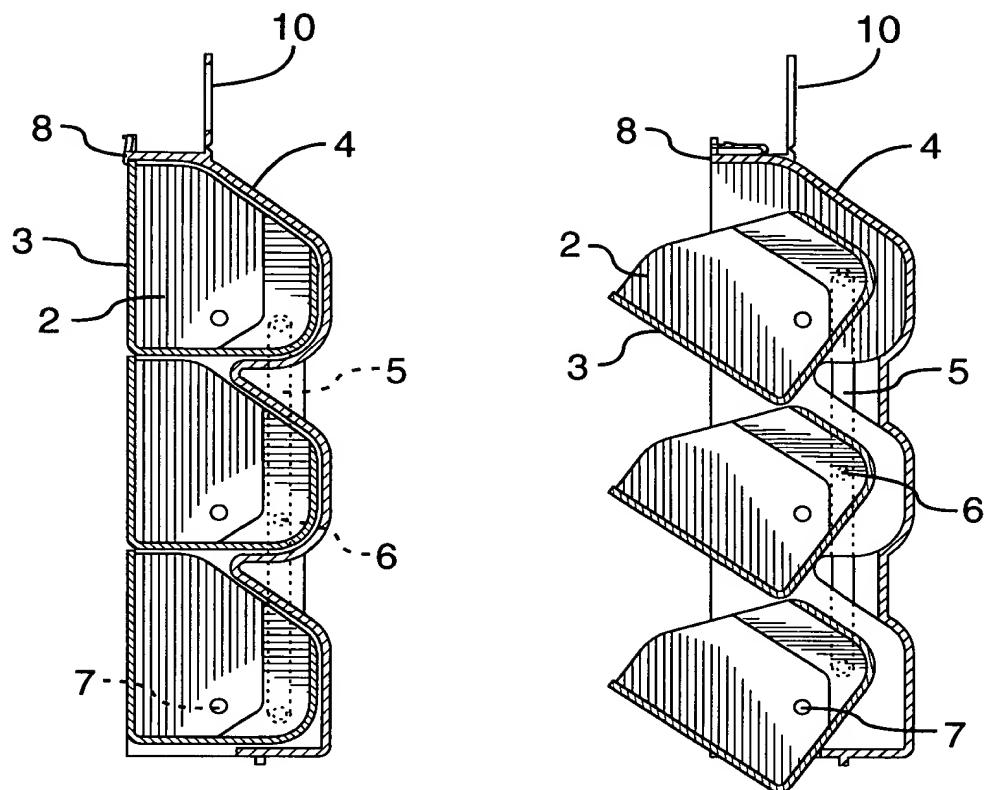


FIG.6

FIG.7

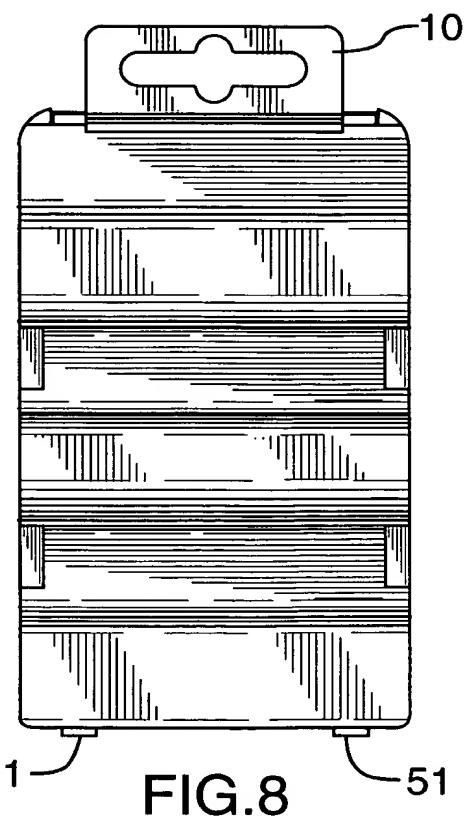


FIG.8

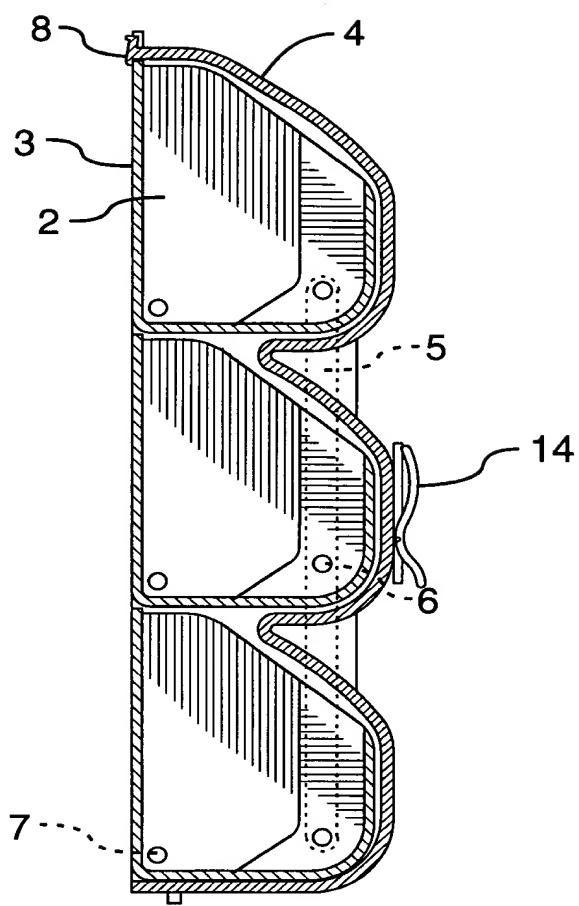


FIG.10

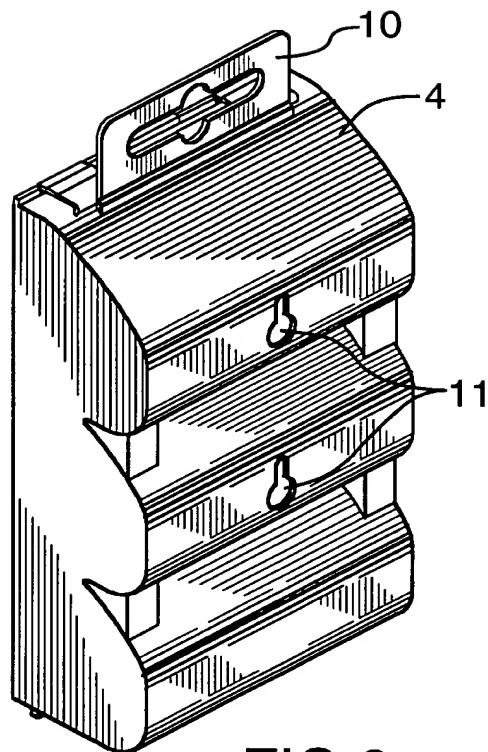


FIG.9

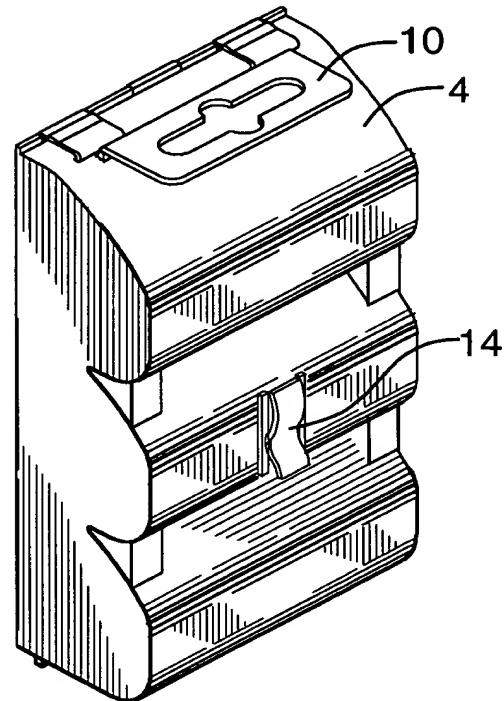


FIG.11

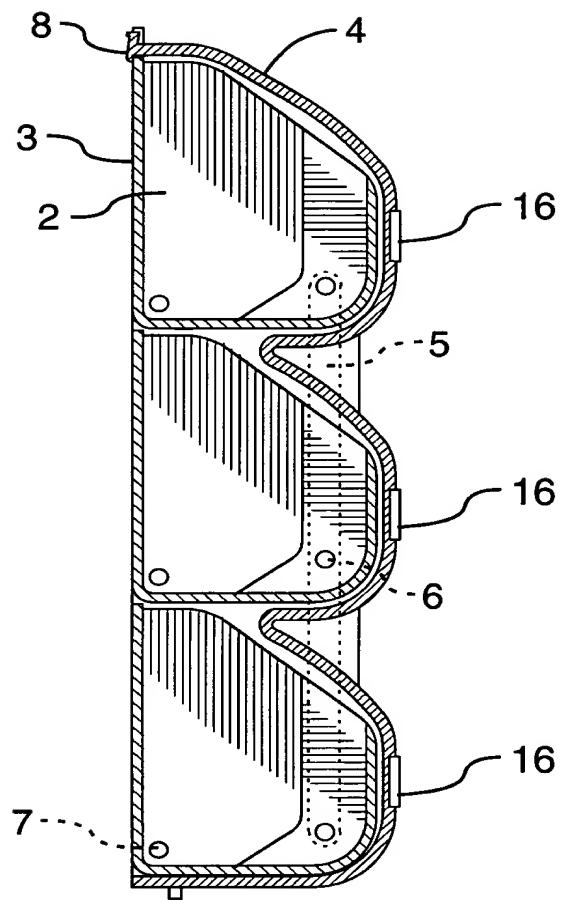


FIG.12

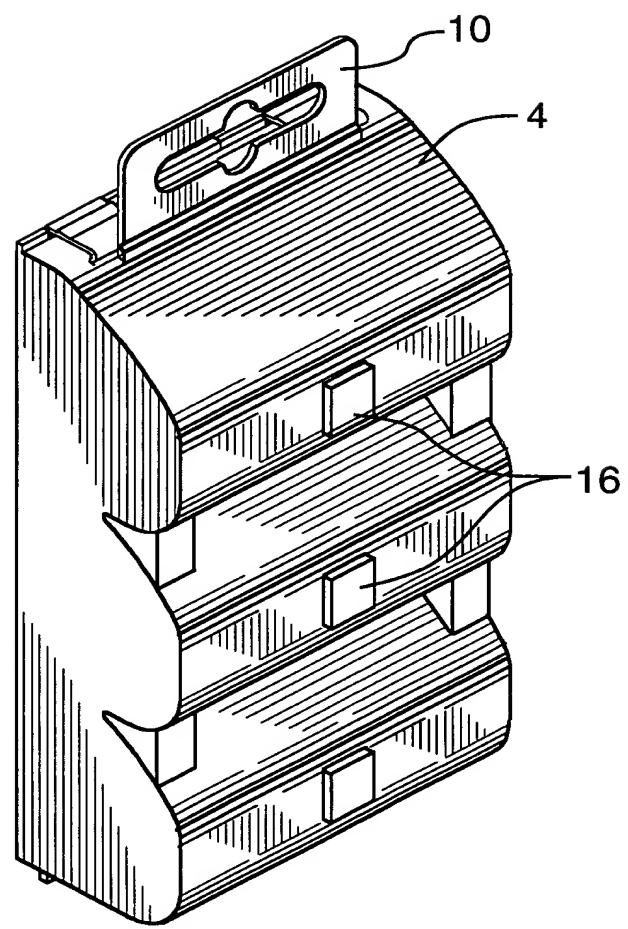


FIG.13

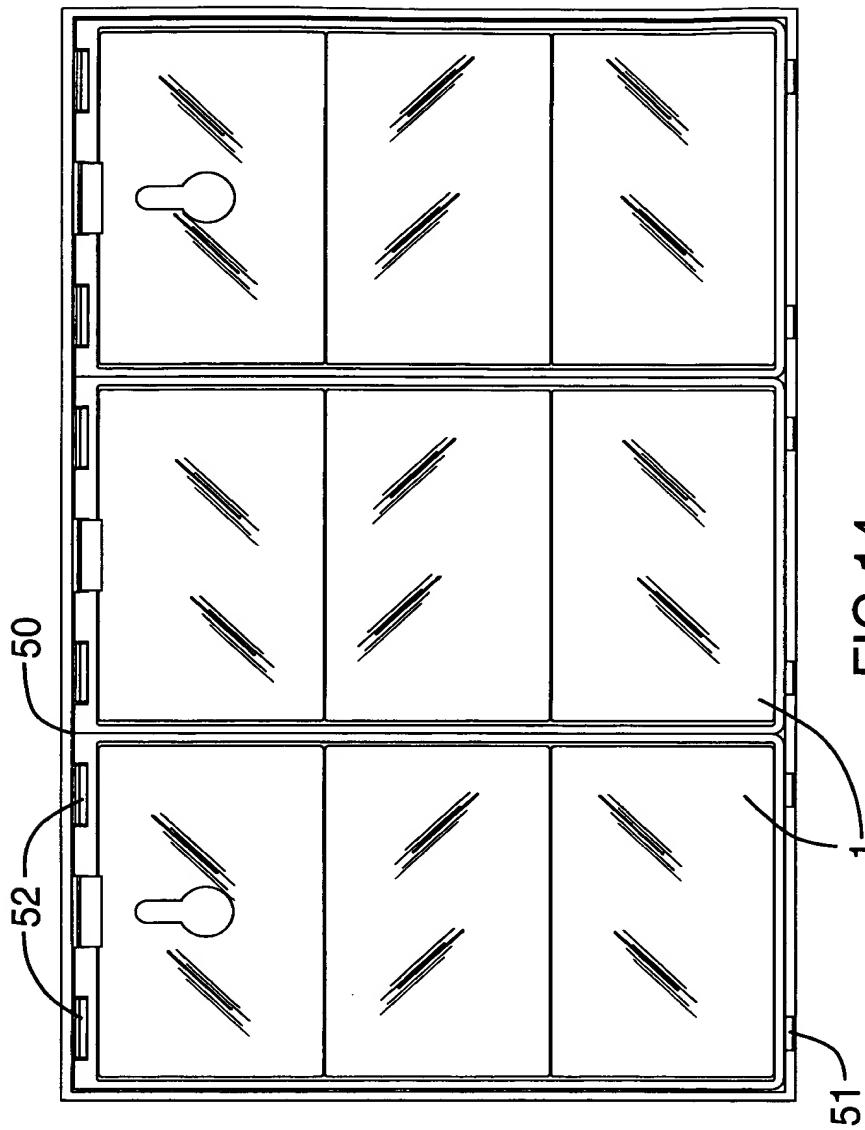
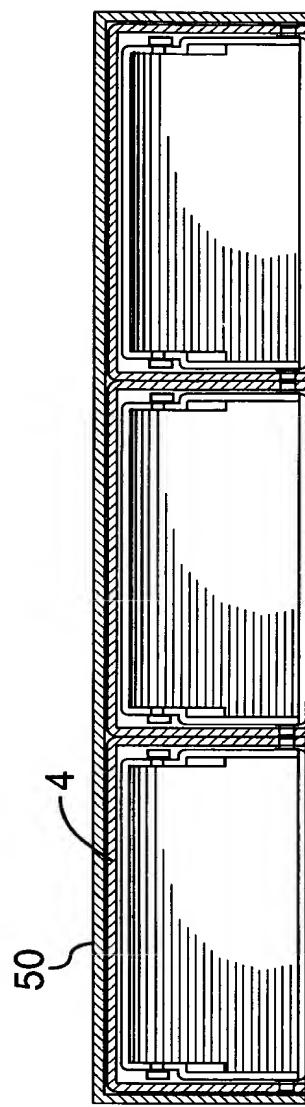
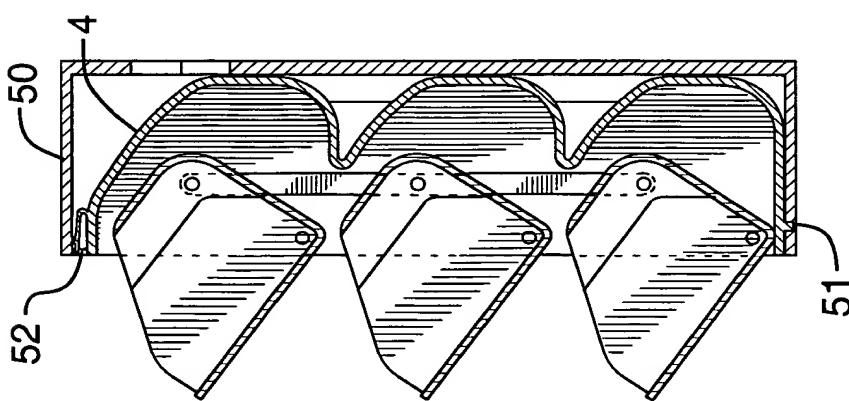


FIG. 14



A cross-sectional diagram of a memory device structure. The structure is bounded by a thick, textured outer layer labeled '50'. Inside this layer, a vertical stack of alternating layers is shown. The top layer is labeled '4'. The stack consists of approximately 15 vertical lines of varying widths, representing different layers of the memory cell. The bottom of the stack is anchored to a horizontal base layer.



51

03292655 - 43220

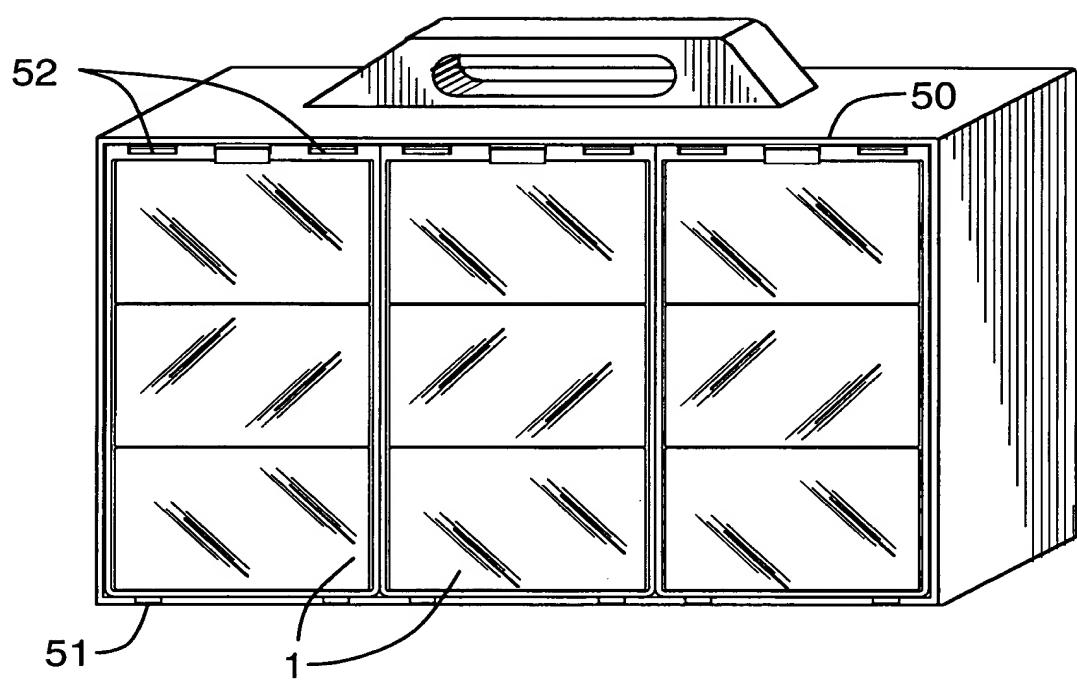


FIG.17

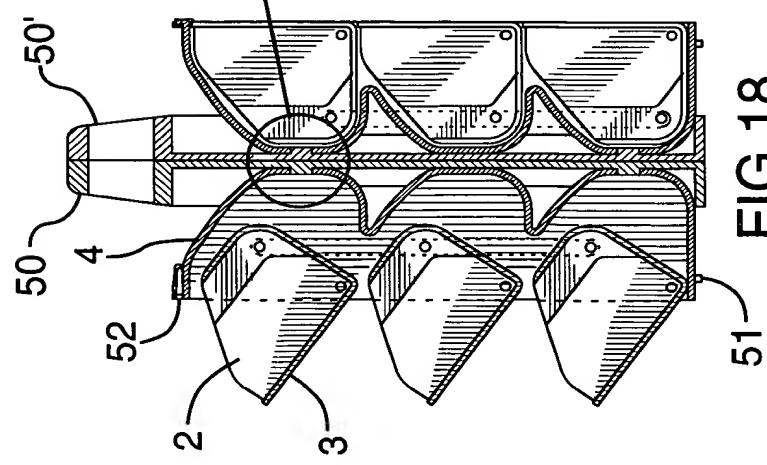


FIG. 18

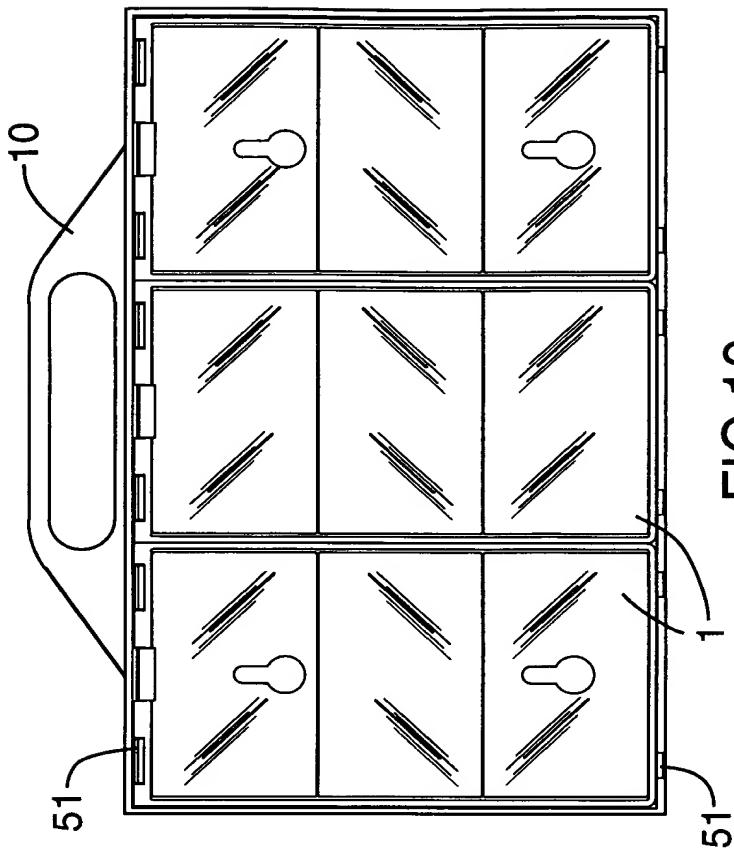


FIG. 19

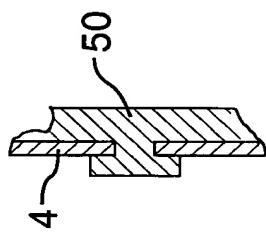


FIG. 18A

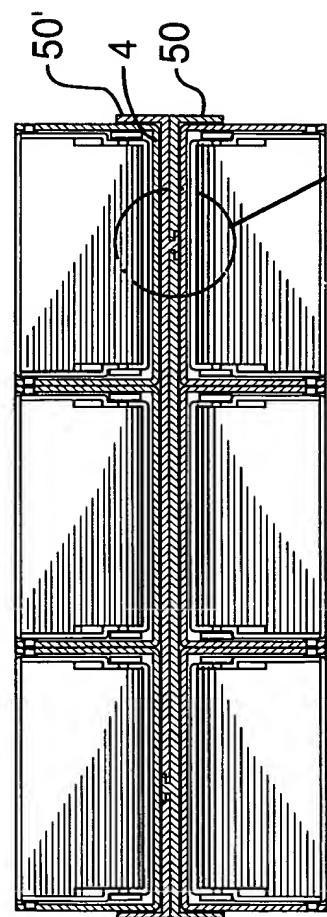


FIG. 20

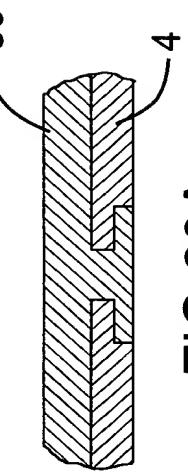


FIG. 20A

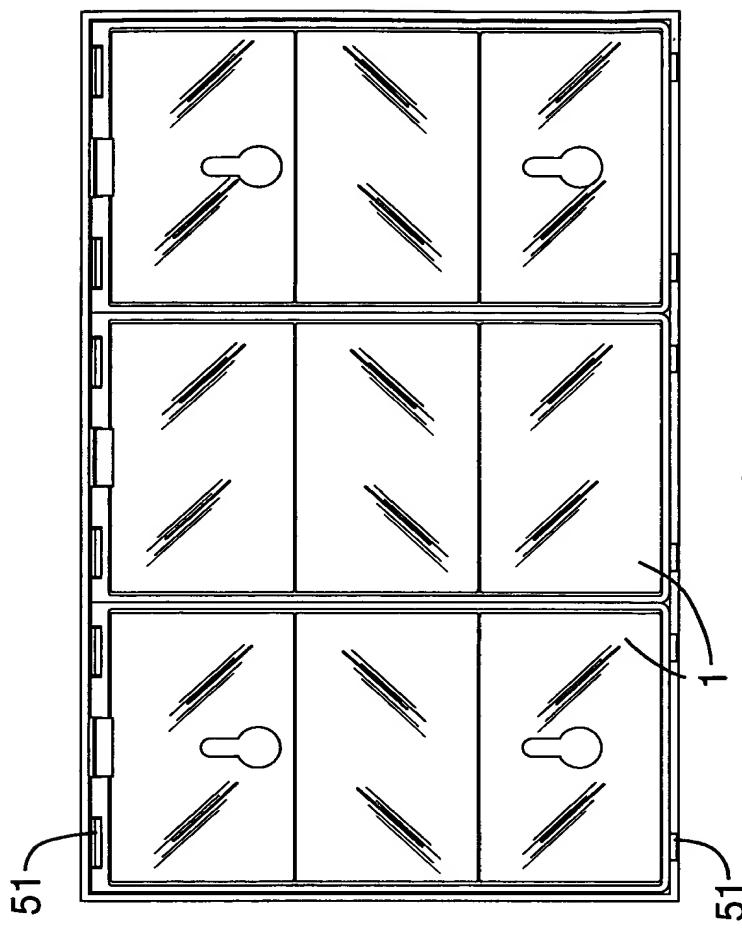


FIG. 22

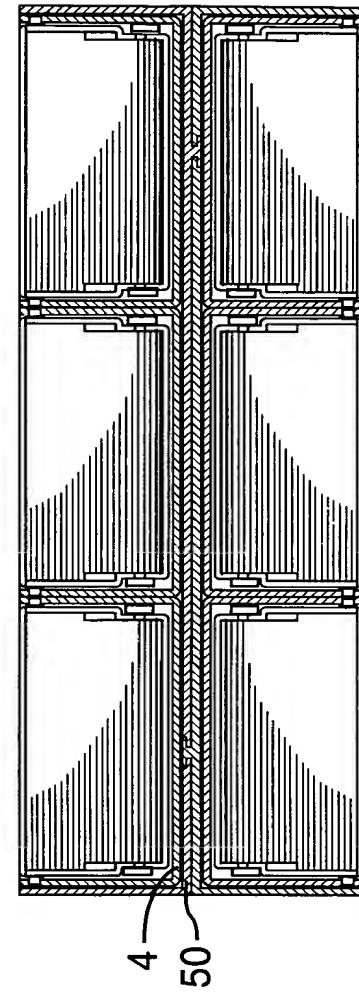
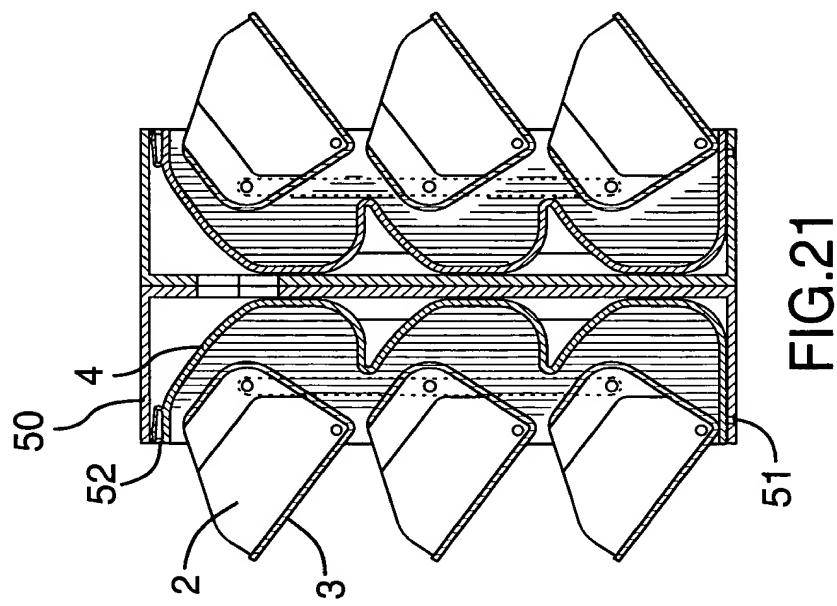
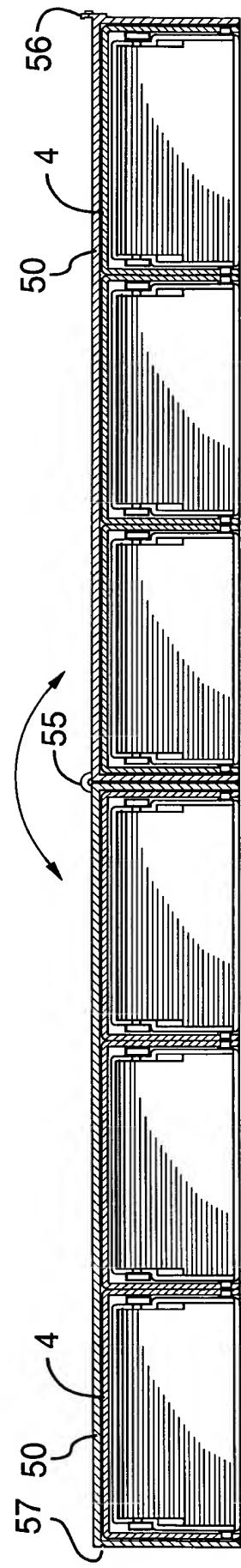
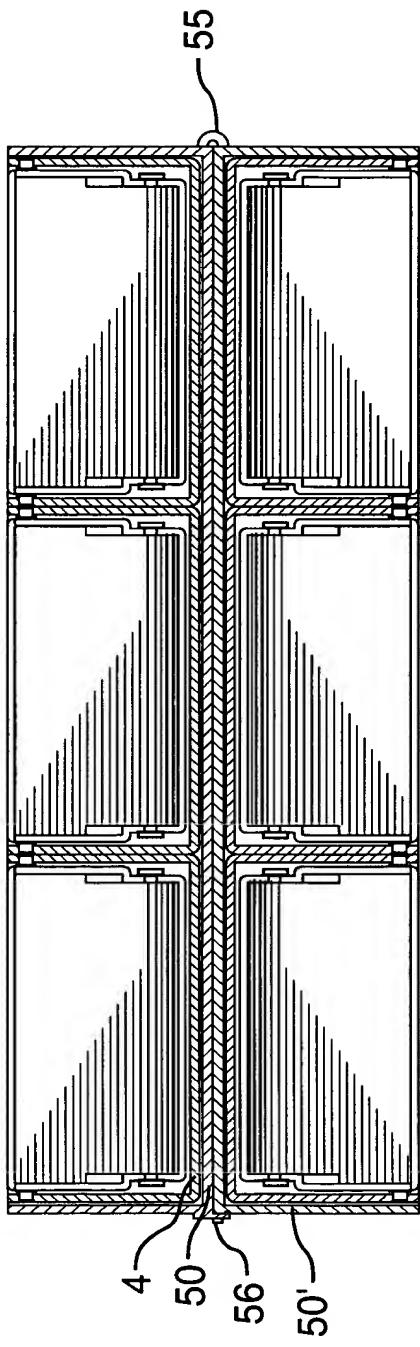


FIG. 23





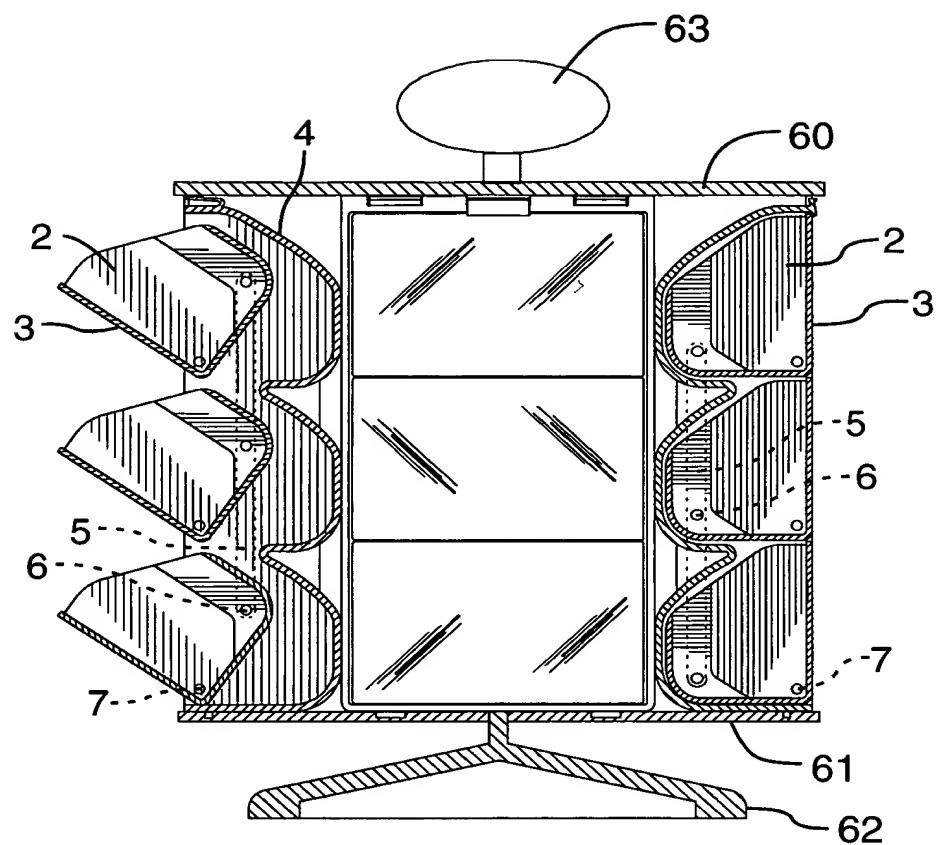


FIG.26

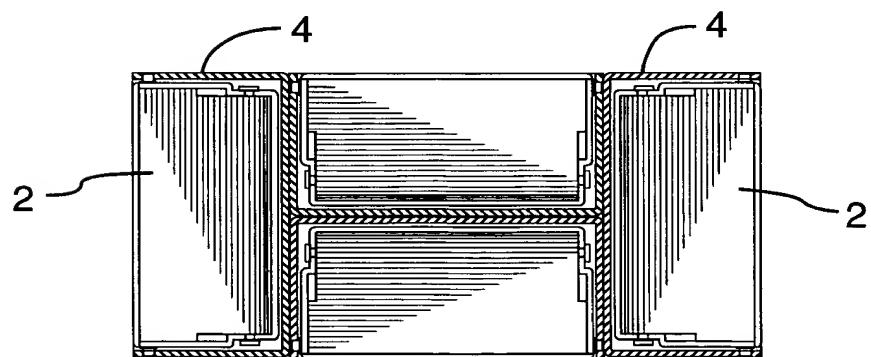


FIG.27

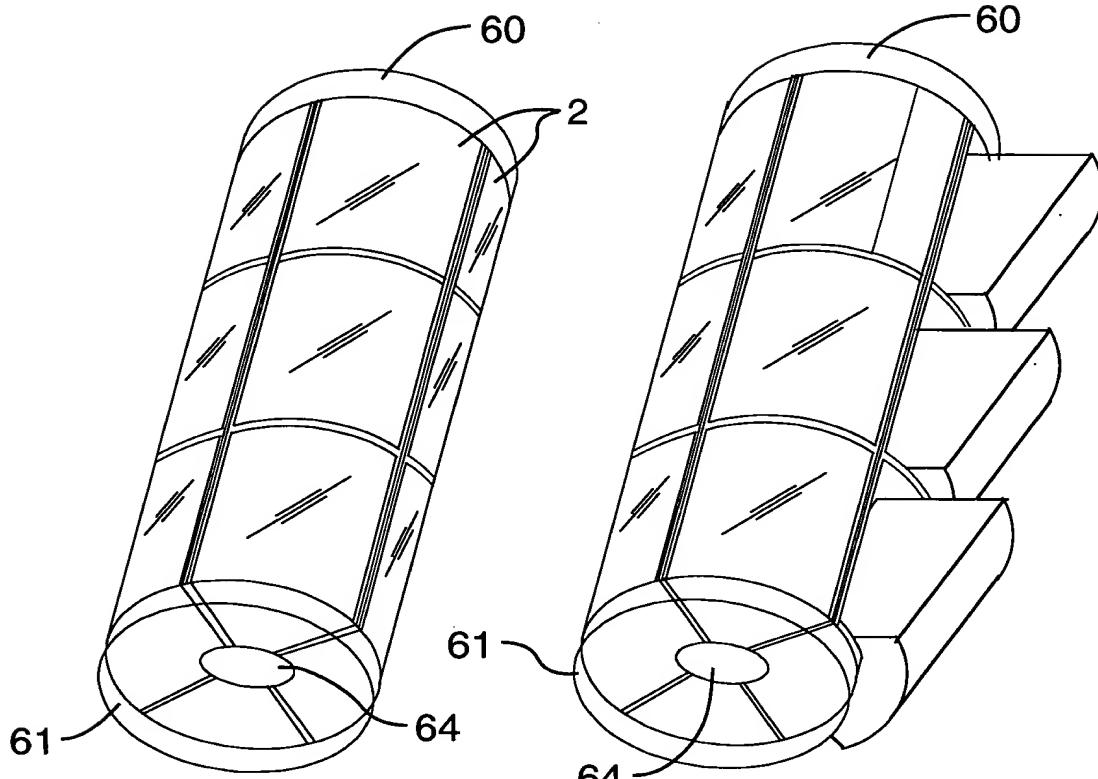


FIG.28

FIG.29

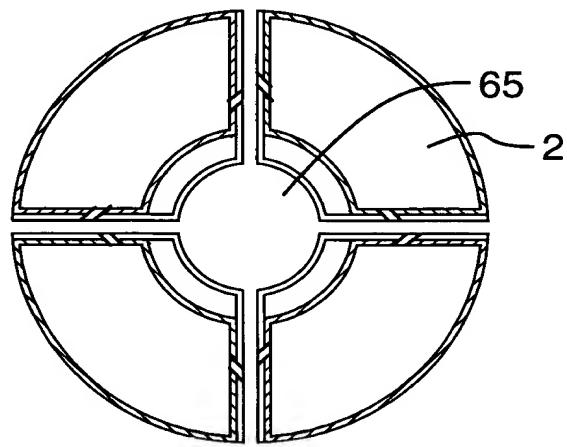


FIG.30

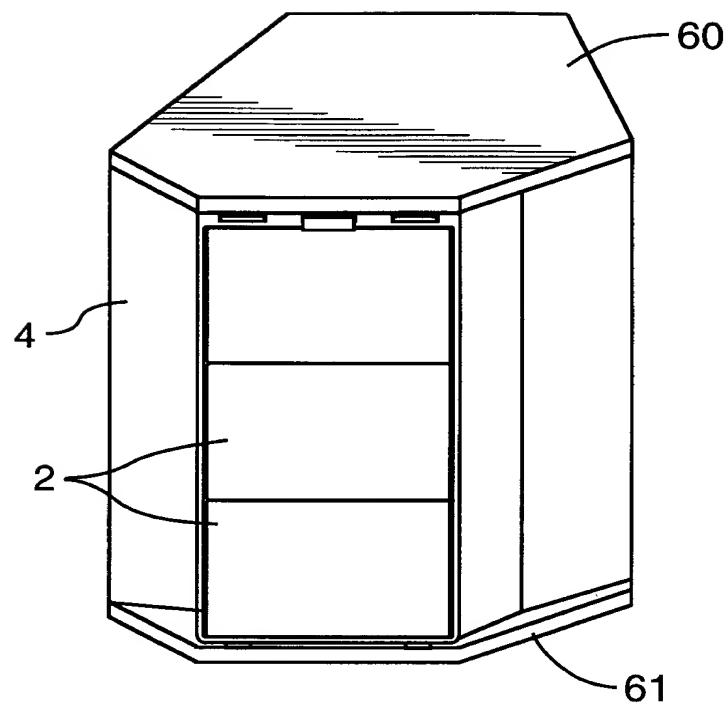


FIG.31

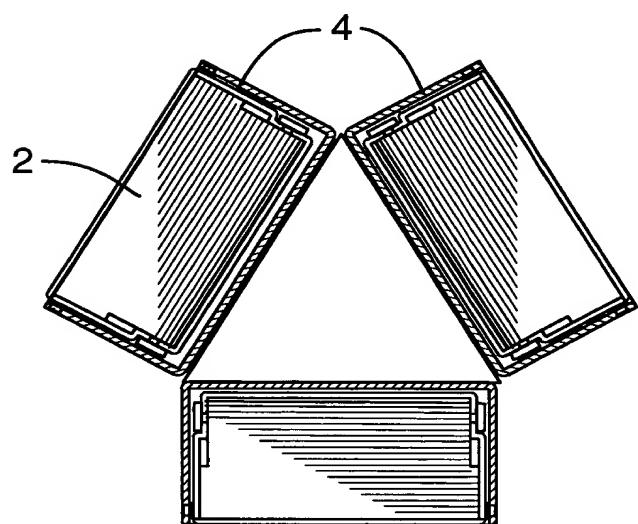


FIG.32

050000055 - 402262

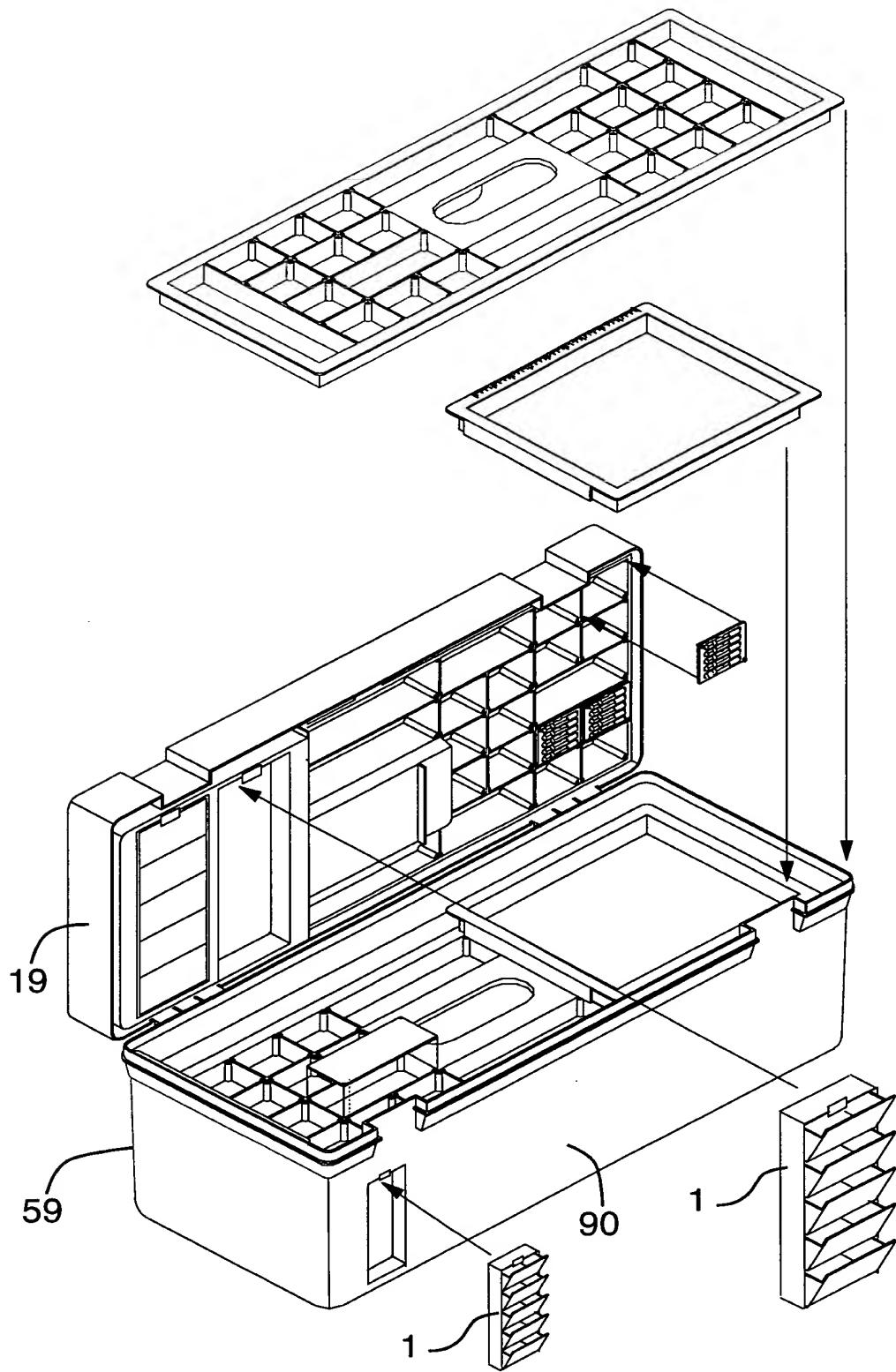


FIG.33

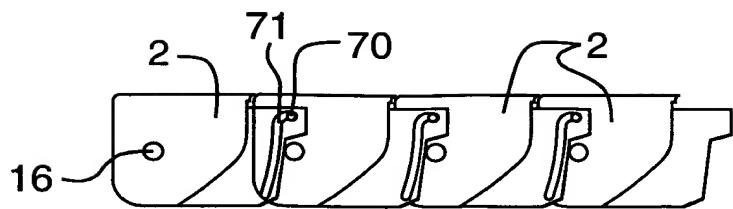


FIG.34

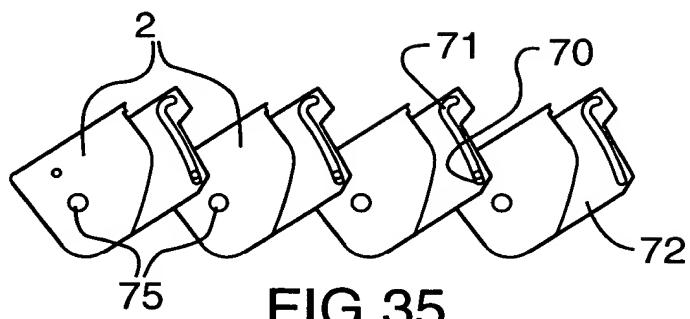


FIG.35

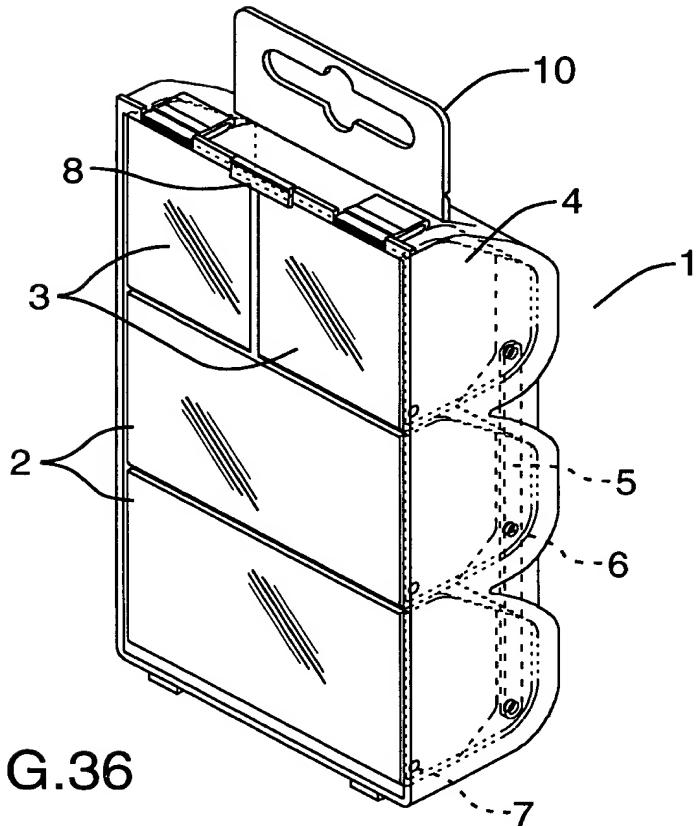


FIG.36

தமிழ்நாடு அரசு கலை மற்றும் கலைஞர்களின் பெருமை

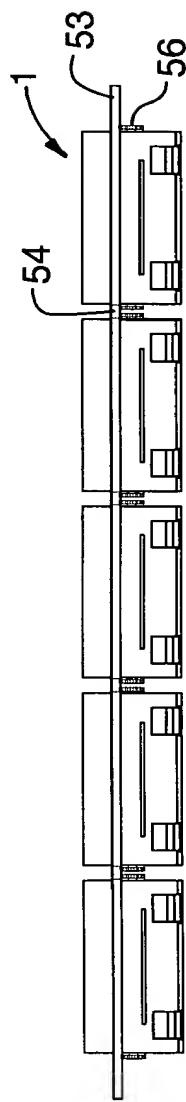


FIG.37C

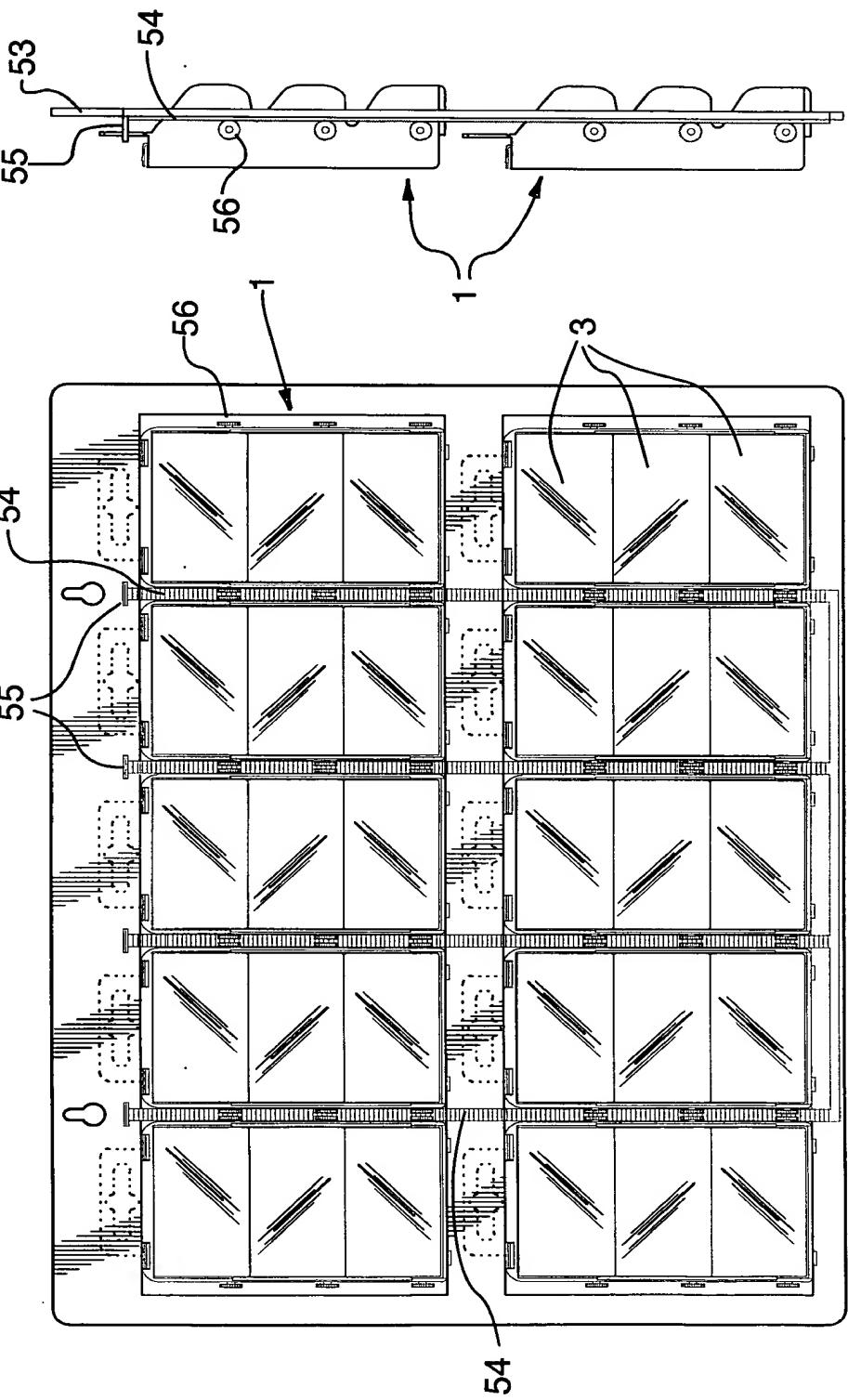


FIG.37A

FIG.37B

20220315-5528650

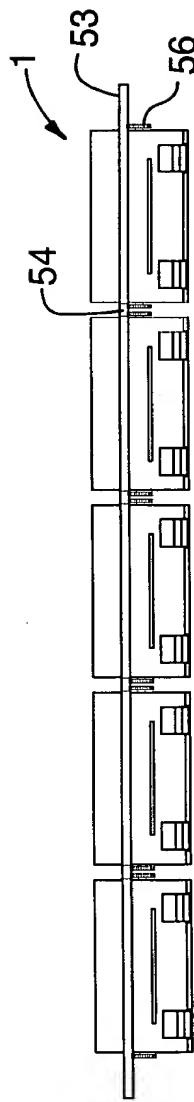


FIG.37F

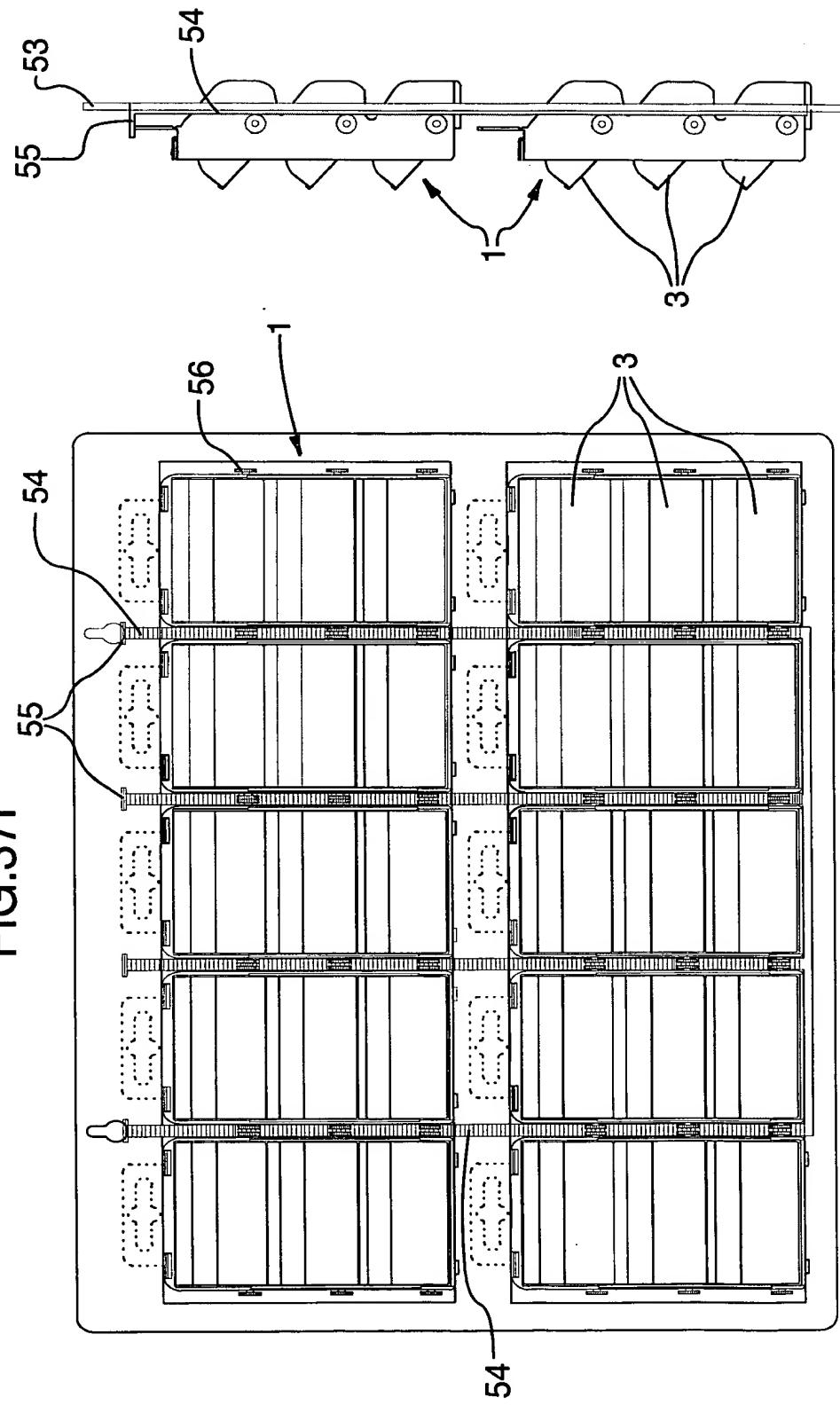


FIG.37D

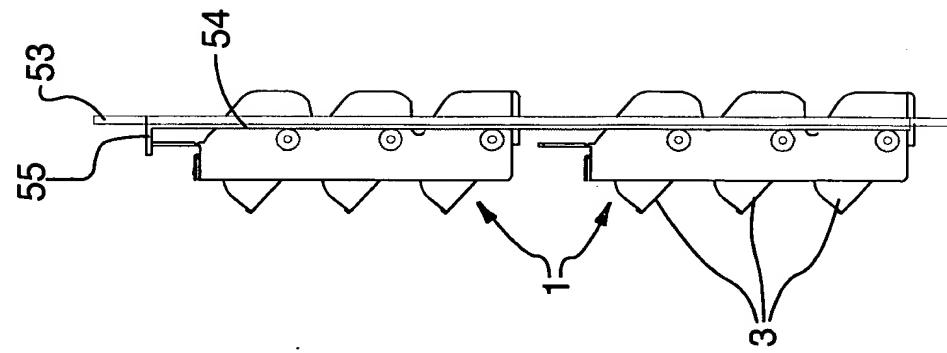


FIG.37E